

Client Reference: P-1841.000-US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re the Application of

BASELMANS et al.

Group Art Unit: 1651

Application No.: 10/814,822

Examiner: Unassigned

Filed: April 1, 2004

Confirmation No.: 5320

For: LITHOGRAPHIC APPARATUS, DEVICE MANUFACTURING METHOD AND DEVICE

MANUFACTURED THEREBY

September 9, 2004

## **INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. 1.56, the attention of the Patent and Trademark Office is hereby directed to the following U.S. patent application(s):

Examiner's Initials	First Inventor	Application No.	Filing Date	Enclosed
	DE SMIT (081468-0309173)	10/820,227	04/08/2004	<ul><li>☑ Specification</li><li>☑ Drawings</li><li>☑ Other: stamped receipt card</li></ul>
	DE SMIT (081468-0309978)	10/860,662	06/04/2004	<ul><li>✓ Specification</li><li>✓ Drawings</li><li>✓ Other: stamped receipt card</li></ul>
	DUINEVELD et al. (081468-0308101)	10/773,461	02/09/2004	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>
	FLAGELLO et al. (081468-0302644)	10/698,012	10/31/2003	<ul><li>☑ Specification</li><li>☑ Drawings</li><li>☑ Other: stamped receipt card</li></ul>
	DE SMIT et al. (081468-0306530)	10/705,804	11/12/2003	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>
	LOF et al. (081468-0306781)	10/705,805	11/12/2003	<ul><li>☑ Specification</li><li>☑ Drawings</li><li>☑ Other: stamped receipt card</li></ul>
	LOF et al. (081468-0306524)	10/705,783	11/12/2003	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt</li></ul>

Examiner's Initials	First Inventor	Application No.	Filing Date	Enclosed
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P 0 9 2004 E 0 9	VAN SANTEN et al. (081468-0307331)	10/743,271	12/23/2003	<ul><li>Specification</li><li>Drawings</li><li>Other: stamped receipt card</li></ul>
* TRADEMAN	MULKENS et al. (081468-0307333)	10/743,266	12/23/2003	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>
	DERKSEN et al. (081468-0306526)	10/705,785	11/12/2003	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>
	SIMON et al. (081468-0307087)	10/724,402	12/01/2003	<ul><li>✓ Specification</li><li>✓ Drawings</li><li>✓ Other: stamped receipt card</li></ul>
	BLEEKER (081468-0306527)	10/715,116	11/18/2003	<ul><li>✓ Specification</li><li>✓ Drawings</li><li>✓ Other: stamped receipt card</li></ul>
	STREEFKERK et al. (081468-0306882)	10/719,683	11/24/2003	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>
	LOF et al. (081468-0306525)	10/705,816	11/12/2003	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>
	DIERICHS (081468-0308270)	10/775,326	02/11/2004	<ul><li>☑ Specification</li><li>☑ Drawings</li><li>☑ Other: stamped receipt card</li></ul>
	LOF et al. (081468-0309957)	10/857,614	06/01/2004	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>
	SUWA et al. (Reissue Application of U.S. Patent No. 6,191,429 B1)	10/367,910	02/19/2003	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☐ Other: stamped receipt card</li></ul>
	BASELMANS et al. (081468-0309488)	10/835,856	05/03/2004	<ul><li>☒ Specification</li><li>☒ Drawings</li><li>☒ Other: stamped receipt card</li></ul>

<sup>\*</sup>The Examiner's initials adjacent a citation indicates he/she has considered the cited application relative to the subject application.

It is respectfully requested that these applications and the art cited therein during examination be expressly considered during the prosecution of this application and be made of record in this application. The identification of the above U.S. patent applications is not to be construed as a waiver of secrecy as to those applications now or upon issuance of the present application as a patent.

<u>PLEASE DO NOT PRINT</u> the above information on the patent which results from this application.

Consideration of each listed application is earnestly solicited since unpublished patent applications are contemplated as IDS material; see the exception in Rule 98(a)(2)(iii) and note the penultimate sentence of MPEP 609.

Further, in keeping with MPEP 609, subsec. C(2), 2nd para., line 10 to end of the paragraph (especially note lines 18-25) PLEASE <u>RETURN</u> A COPY OF <u>THIS LETTER</u> with the Examiner's initials adjacent each above listing so that applicant will know that each listed application has been considered as required by PTO policy.

Secondly, please consider each document which is listed on the attached Form PTO-1449 and return a copy of that form with the Examiner's initials adjacent each citation, a copy of each document enclosed except for any U.S. patents and published patent applications. It is respectfully requested that these documents listed on the Form PTO-1449 be expressly considered during the prosecution of this application, and that the documents be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed before the mailing date of the first Office Action on the merits in the present application. No certification or fee is required.

Respectfully Submitted,

PILLSBURY WINTHROP LLP

Jean-Paul G. Hoffinan Registration Number 42663 Customer Number: 00909

P.O. Box 10500 McLean, VA 22102

Telephone: (703) 905-2000 Facsimile: (703) 905-2500

FORM PTO-1449 (modified) Atty. М# Client Ref. To: U.S. Department of Commerce Dkt. No. (PW FORM PAT-1449) Patent and Trademark Office SEP 0 9 2004 309022 P-1841.000-US INFORMATION DISCLOSURE STATEMENTADE Applicant: BASELMANS et al. BY APPLICANT Appln. No. 10/814,822 Filing Date: April 1, 2004 Date: Page 1 of Examiner: Unknown September 9, 2004 Group Art Unit: 1651 **U.S. PATENT DOCUMENTS** Examiner's Document Date Name Class Sub Filing Date Initials\* Number MM/YYYY (Family Name of First Inventor) Class (if appropriate) 3,573,975 04/1971 DHAKA et al. 212 AR 117 03/1972 BR 3,648,587 STEVENS 95 44 CR 4,346,164 08/1982 TABARELLI et al. 430 311 DR 4,390,273 06/1983 LOEBACH et al. 355 125 08/1983 ER 4,396,705 AKEYAMA et al. 430 326 FR 4,480,910 11/1984 TAKANASHI et al. 355 30 04/1985 GR 4,509,852 TABARELLI et al. 30 355 HR 08/1991 53 5,040,020 RAUSCHENBACH et al. 355 IR 5,121,256 06/1992 CORLE et al. 359 664 03/1997 JR 5.610.683 TAKAHASHI 355 **|**53 KR 5,715,039 02/1998 FUKUDA et al. 53 355 10/1998 LR 5,825,043 SUWA 250 548 5,900,354 05/1999 **BATCHELDER** MR 430 395 02/2001 SUWA NR |6,191,429 250 548 FOREIGN PATENT DOCUMENTS English Abstract Translation Readily Document Date Country Inventor Name Available MM/YYYY Number Enclosed No Enclosed No PCT OR WO 99/49504 09/1999 FUKAMI et al. Х Х PR EP 0023231 02/1981 **EUROPE** TABARELLI et al. Х QR EP 0418427 03/1991 **EUROPE** MIYAKE Х Х RR IEP 1039511 09/2000 **EUROPE** Χ MURAKAMI et al. Х SR DD 224448 07/1985 **GERMANY** HESSE et al. Х TR DD 242880 02/1987 GERMANY **KUCH** Х UR FR 2474708 07/1981 **FRANCE** Х LETELLIER VR JP 62-065326 03/1987 JAPAN MORIUCHI Х WR JP 62-121417 06/1987 **JAPAN** NAKAZAWA Χ XR JP 63-157419 06/1988 **JAPAN** X NAKASUJI YR JP 04-305915 10/1992 **JAPAN** OZEKI et al. Х JP 04-305917 10/1992 **JAPAN** OZEKI et al. Х AAR JP 06-124873 05/1994 **JAPAN TAKAHASHI** Х Х OTHER (Including in this order Author, Title, Periodical Name, Date, Pertinent Pages, etc.) BBR|M. SWITKES et al., "Immersion Lithography at 157 nm", MIT Lincoln Lab, Orlando 2001-1, December 17, 2001 CCRM. SWITKES et al., "Immersion Lithography at 157 nm", J. Vac. Sci. Technol. B., Vol. 19, No. 6, November/December 2001, pp. 2353-2356 DDRM. SWITKES et al., "Immersion Lithography: Optics for the 50 nm Node", 157 Anyers-1, September 4, 2002 Examiner Date Considered: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if **EXAMINER:** 

not in conformance and not considered. Include copy of this form with next communication to Applicant.

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